IR HiRel
An Infineon Technologies Company

IRHN9150
JANSR2N7422U

RADIATION HARDENED POWER MOSFET SURFACE MOUNT (SMD-1)

100V, P-CHANNEL
REF: MIL-PRF-19500/662
RAD Hard™ HEXFET® TECHNOLOGY

Product Summary

Part Number	Radiation Level	RDS(on)	I_D	QPL Part Number
IRHN9150	100 kRads(Si)	0.080Ω	-22A	JANSR2N7422U
IRHN93150	300 kRads(Si)	0.080Ω	-22A	JANSF2N7422U

SMD - 1

Description

IR HiRel RADHard™ HEXFET® MOSFET technology provides high performance power MOSFETs for space applications. This technology has long history of proven performance and reliability in satellite applications. These devices have been characterized for both Total Dose and Single Event Effects (SEE). The combination of low RDS(on) and low gate charge reduces the power losses in switching applications such as DC to DC converters and motor control. These devices retain all of the well established advantages of MOSFETs such as voltage control, fast switching and temperature stability of electrical parameters.

Features

- Single Event Effect (SEE) Hardened
- Low RDS(on)
- Low Total Gate Charge
- Proton Tolerant
- Simple Drive Requirements
- Hermetically Sealed
- Surface Mount
- Ceramic Package
- Light Weight
- ESD Rating: Class 2 per MIL-STD-750, Method 1020

Absolute Maximum Ratings — Pre-Irradiation

Symbol	Parameter	Value	Units
I_{D1} @ V_{GS} = -12V, T_C = 25°C	Continuous Drain Current	-22	A
I_{D2} @ V_{GS} = -12V, T_C = 100°C	Continuous Drain Current	-14	
I_{DM} @ T_C = 25°C	Pulsed Drain Current ①	-88	
P_D @ T_C = 25°C	Maximum Power Dissipation	150	W
	Linear Derating Factor	1.2	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy ②	500	mJ
I_{AR}	Avalanche Current ①	-22	A
E_{AR}	Repetitive Avalanche Energy ①	15	mJ
dv/dt	Peak Diode Recovery dv/dt ③	-23	V/ns
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 150	°C
	Package Mounting Surface Temp.	300 (for 5s)	
	Weight	2.6 (Typical)	g

For Footnotes, refer to the page 2.

Electrical Characteristics @ Tj = 25°C (Unless Otherwise Specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	-100	—	—	V	V_{GS} = 0V, I_D = -1.0mA
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	-0.093	—	V/°C	Reference to 25°C, I_D = -1.0mA
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	0.080	Ω	V_{GS} = -12V, I_{D2} = -14A ④
		—	—	0.085		V_{GS} = -12V, I_{D1} = -22A ④
$V_{GS(th)}$	Gate Threshold Voltage	-2.0	—	-4.0	V	V_{DS} = V_{GS}, I_D = -1.0mA
Gfs	Forward Transconductance	11	—	—	S	V_{DS} = -15V, I_{D2} = -14A ④
I_{DSS}	Zero Gate Voltage Drain Current	—	—	-25	μA	V_{DS} = -80V, V_{GS} = 0V
		—	—	-250		V_{DS} = -80V, V_{GS} = 0V, T_J = 125°C
I_{GSS}	Gate-to-Source Leakage Forward	—	—	-100	nA	V_{GS} = -20V
	Gate-to-Source Leakage Reverse	—	—	100		V_{GS} = 20V
Q_G	Total Gate Charge	—	—	200	nC	I_{D1} = -22A
Q_{GS}	Gate-to-Source Charge	—	—	35		V_{DS} = -50V
Q_{GD}	Gate-to-Drain ('Miller') Charge	—	—	48		V_{GS} = -12V
$t_{d(on)}$	Turn-On Delay Time	—	—	40	ns	V_{DD} = -50V
tr	Rise Time	—	—	170		I_{D1} = -22A
$t_{d(off)}$	Turn-Off Delay Time	—	—	190		R_G = 2.35Ω
t_f	Fall Time	—	—	190		V_{GS} = -12V
Ls +L_D	Total Inductance	—	4.0	—	nH	Measured from the center of drain pad to center of source pad
C_{iss}	Input Capacitance	—	4300	—	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	—	1100	—		V_{DS} = -25V
C_{rss}	Reverse Transfer Capacitance	—	310	—		f = 1.0MHz

Source-Drain Diode Ratings and Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
I_S	Continuous Source Current (Body Diode)	—	—	-22	A	
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	-88		
V_{SD}	Diode Forward Voltage	—	—	-3.0	V	T_J = 25°C, I_S = -22A, V_{GS} = 0V④
t_{rr}	Reverse Recovery Time	—	—	300	ns	T_J = 25°C, I_F = -22A, V_{DD} ≤ -50V
Q_{rr}	Reverse Recovery Charge	—	—	1.5	μC	di/dt = -100A/μs ④
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D)				

Thermal Resistance

Symbol	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	—	0.83	°C/W
$R_{\theta J\text{-}PCB}$	Junction-to-PC board (soldered to a 1"sq. copper-clad board)	—	6.6	—	

Footnotes:

① Repetitive Rating; Pulse width limited by maximum junction temperature.

② V_{DD} = -25V, starting T_J = 25°C, L = 2.1mH, Peak I_L = -22A, V_{GS} = -12V

③ I_{SD} ≤ -22A, di/dt ≤ -450A/μs, V_{DD} ≤ -100V, T_J ≤ 150°C

④ Pulse width ≤ 300 μs; Duty Cycle ≤ 2%

⑤ Total Dose Irradiation with V_{GS} Bias. -12 volt V_{GS} applied and V_{DS} = 0 during irradiation per MIL-STD-750, Method 1019, condition A.

⑥ Total Dose Irradiation with V_{DS} Bias. -80 volt V_{DS} applied and V_{GS} = 0 during irradiation per MIL-STD-750, Method 1019, condition A.

Radiation Characteristics

IR HiRel Radiation Hardened MOSFETs are tested to verify their radiation hardness capability. The hardness assurance program at IR HiRel is comprised of two radiation environments. Every manufacturing lot is tested for total ionizing dose (per notes 5 and 6) using the TO-3 package. Both pre- and post-irradiation performance are tested and specified using the same drive circuitry and test conditions in order to provide a direct comparison.

Table1. Electrical Characteristics @ Tj = 25°C, Post Total Dose Irradiation ⑤⑥

Symbol	Parameter	100 kRads (Si)[1]		300k Rads (Si)[2]		Units	Test Conditions
		Min.	Max.	Min.	Max.		
BV_{DSS}	Drain-to-Source Breakdown Voltage	-100	—	-100	—	V	V_{GS} = 0V, I_D = -1.0mA
$V_{GS(th)}$	Gate Threshold Voltage	-2.0	-4.0	-2.0	-5.0	V	V_{DS} = V_{GS}, I_D = -1.0mA
I_{GSS}	Gate-to-Source Leakage Forward	—	-100	—	-100	nA	V_{GS} = -20V
I_{GSS}	Gate-to-Source Leakage Reverse	—	100	—	100	nA	V_{GS} = 20V
I_{DSS}	Zero Gate Voltage Drain Current	—	-25	—	-25	µA	V_{DS} = -80V, V_{GS} = 0V
$R_{DS(on)}$	Static Drain-to-Source ④ On-State Resistance (TO-3)	—	0.080	—	0.080	Ω	V_{GS} = -12V, I_{D2} = -14A
$R_{DS(on)}$	Static Drain-to-Source ④ On-State Resistance (SMD-1)	—	0.080	—	0.080	Ω	V_{GS} = -12V, I_{D2} = -14A
V_{SD}	Diode Forward Voltage ④	—	-3.0	—	-3.0	V	V_{GS} = 0V, I_S = -22A

1. Part numbers IRHN9150 (JANSR2N7422U)
2. Part numbers IRHN93150 (JANSF2N7422U)

IR HiRel radiation hardened MOSFETs have been characterized in heavy ion environment for Single Event Effects (SEE). Single Event Effects characterization is illustrated in Fig. a and Table 2.

Table 2. Typical Single Event Effect Safe Operating Area

Ion	LET (MeV/(mg/cm²))	Energy (MeV)	Range (µm)	VDS (V)				
				@ VGS = 0V	@ VGS = 5V	@ VGS = 10V	@ VGS = 15V	@ VGS = 20V
Cu	28	285	43	-100	-100	-100	-70	-60
Br	36.8	305	39	-100	-100	-70	-50	-40
I	59.9	345	32.8	-60	—	—	—	—

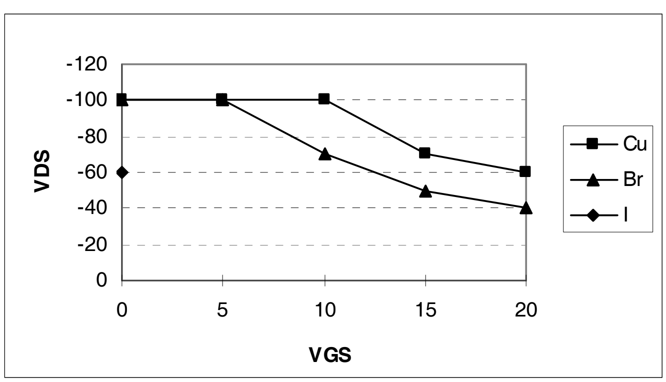


Fig a. Typical Single Event Effect, Safe Operating Area

For Footnotes, refer to the page 2.

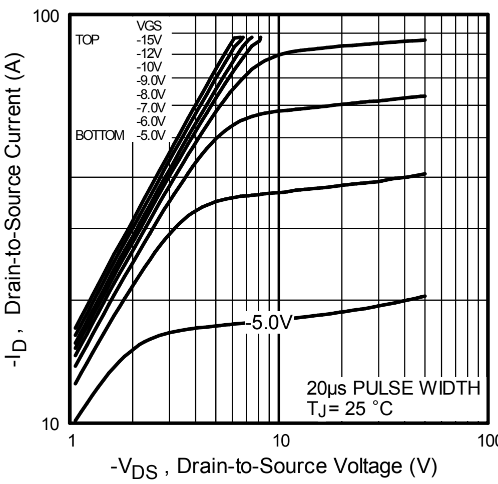


Fig 1. Typical Output Characteristics

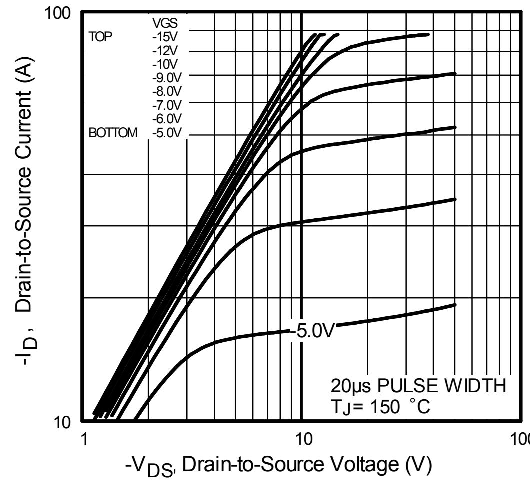


Fig 2. Typical Output Characteristics

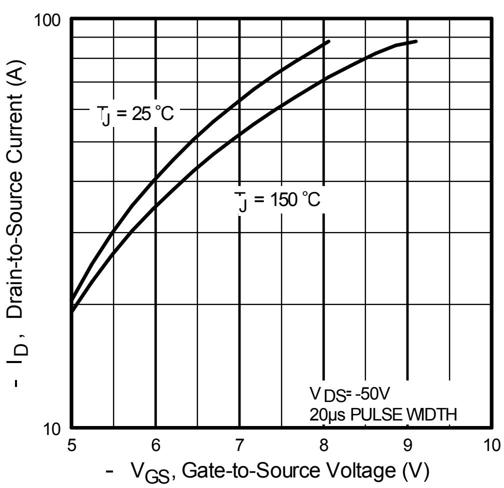


Fig 3. Typical Transfer Characteristics

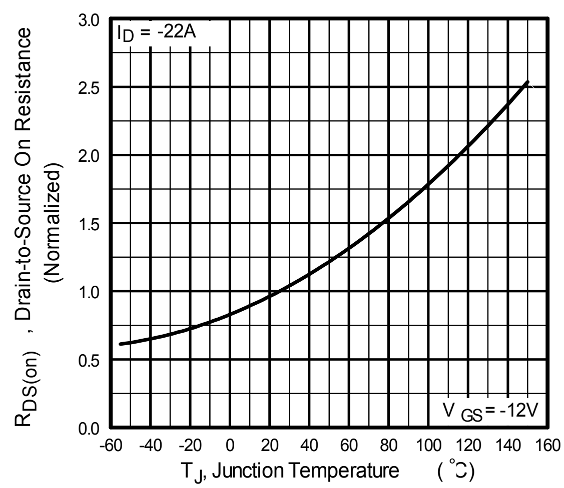


Fig 4. Normalized On-Resistance Vs. Temperature

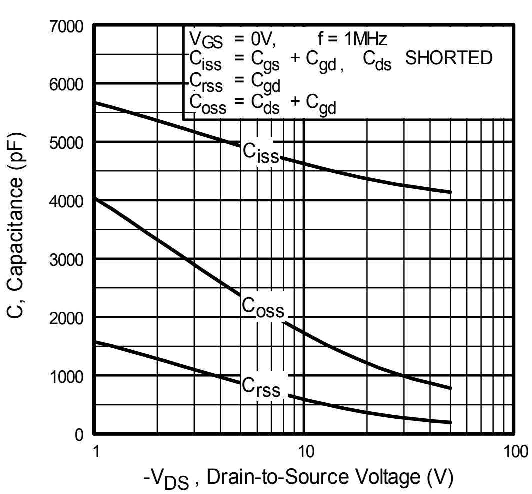


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

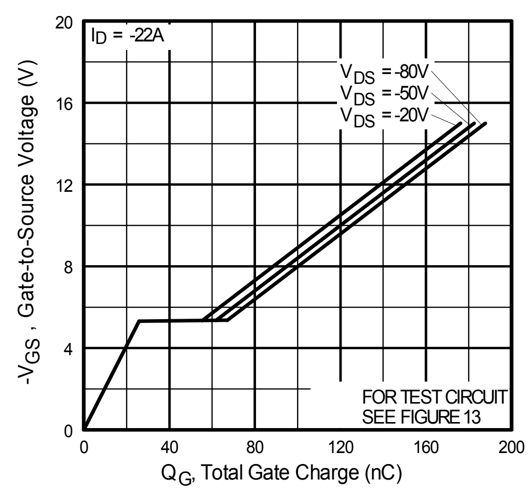


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

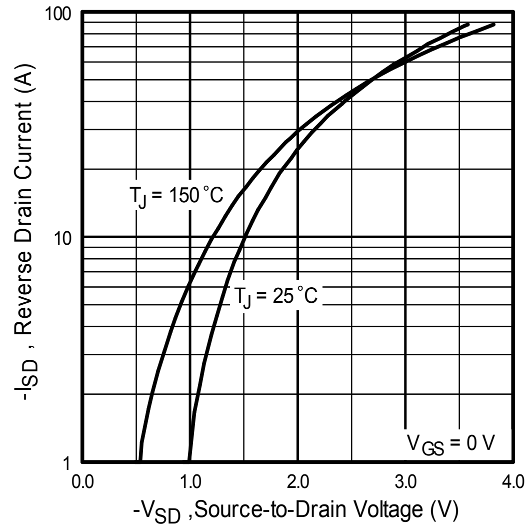


Fig 7. Typical Source-Drain Diode Forward Voltage

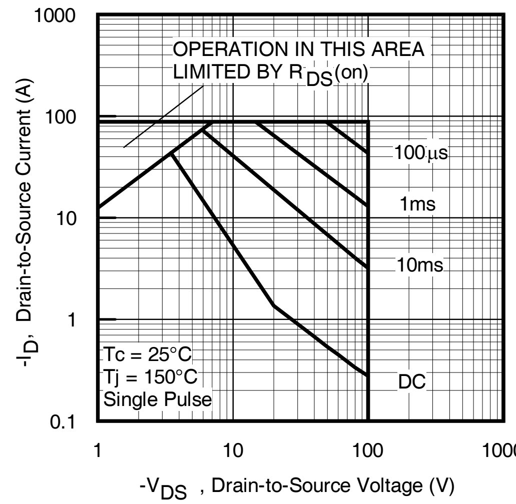


Fig 8. Maximum Safe Operating Area

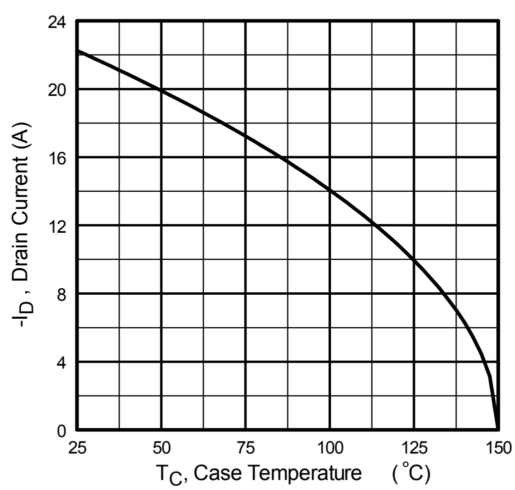


Fig 9. Maximum Drain Current Vs. Case Temperature

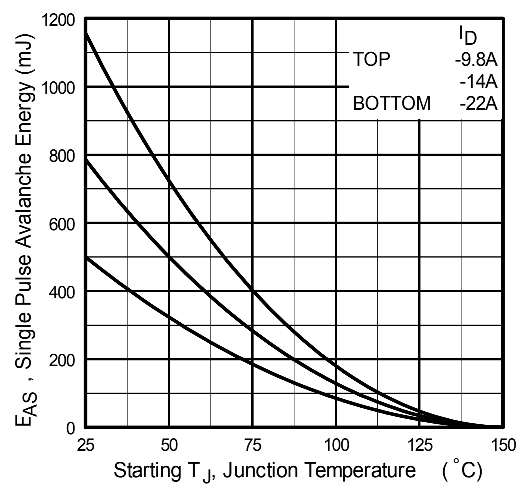


Fig 10. Maximum Avalanche Energy Vs. Drain Current

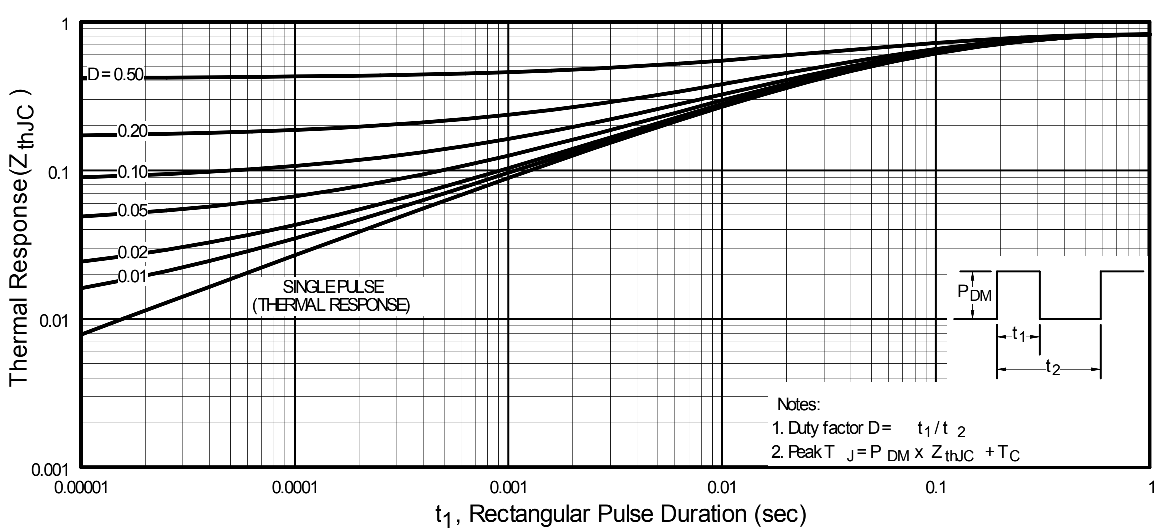


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

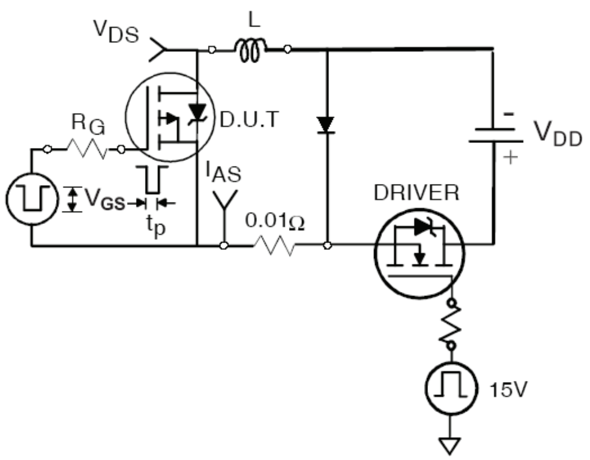


Fig 12a. Unclamped Inductive Test Circuit

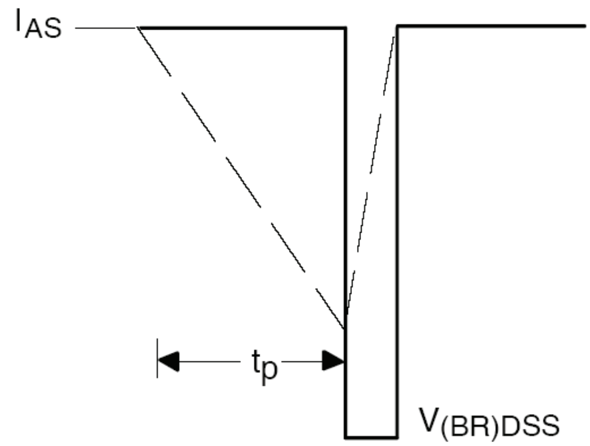


Fig 12b. Unclamped Inductive Waveforms

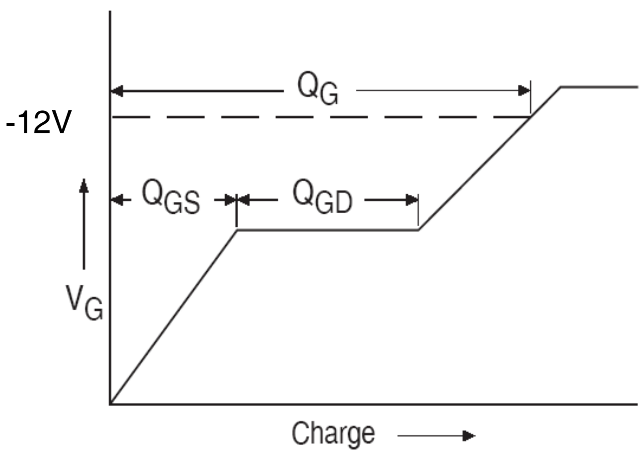


Fig 13a. Basic Gate Charge Waveform

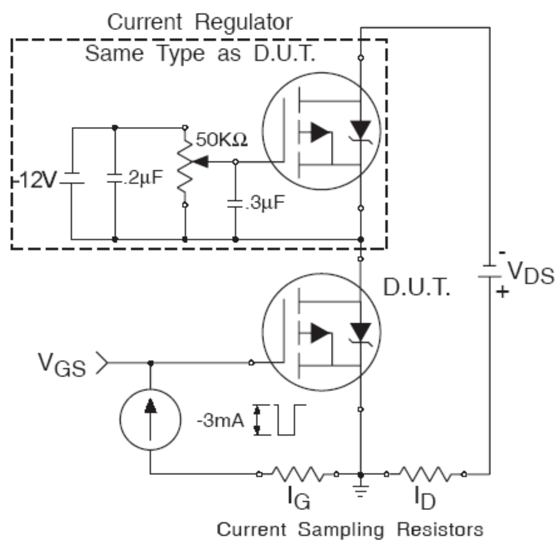


Fig 13b. Gate Charge Test Circuit

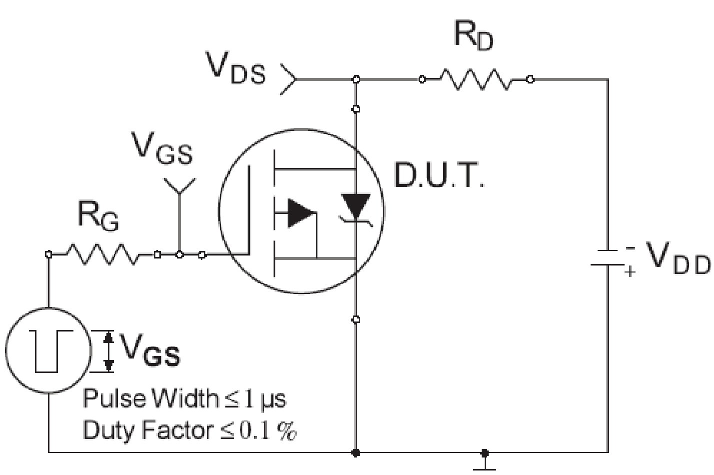


Fig 14a. Switching Time Test Circuit

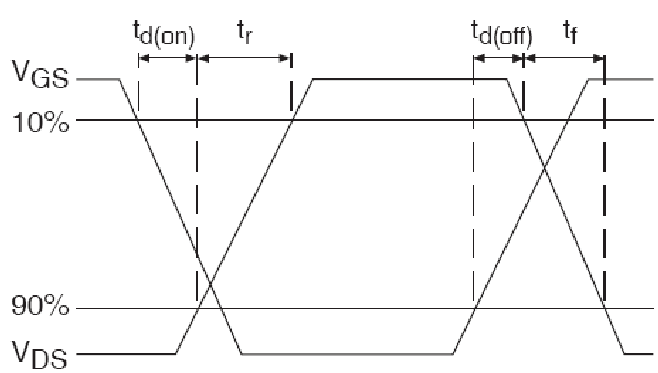
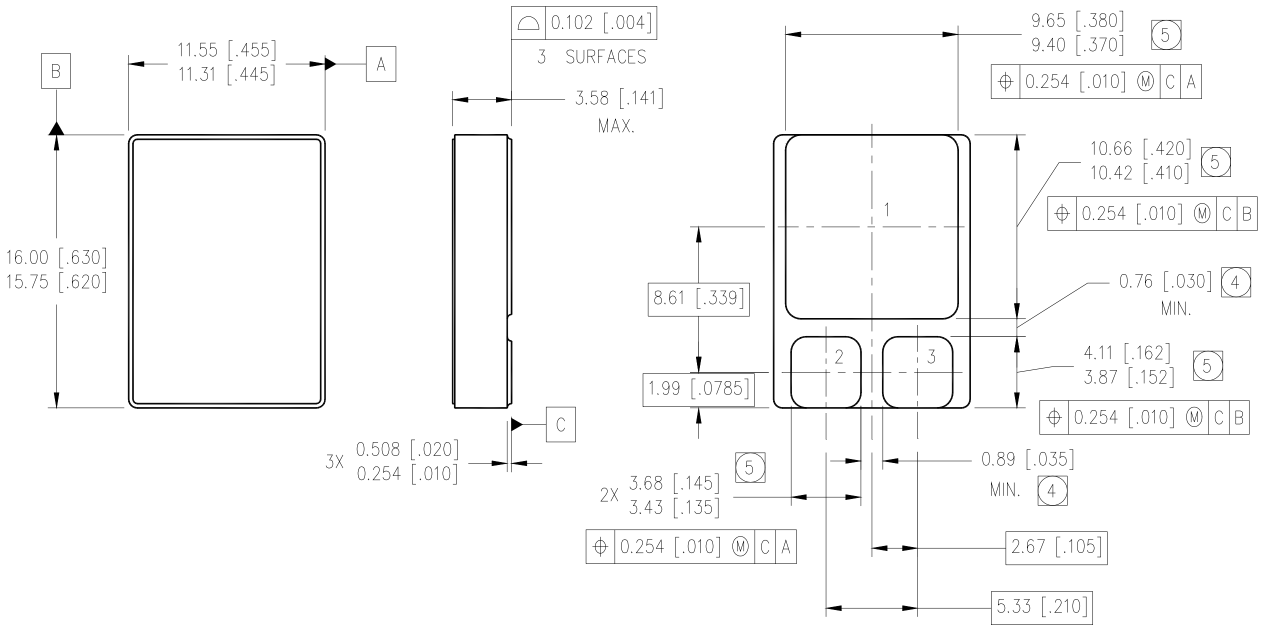


Fig 14b. Switching Time Waveforms

Case Outline and Dimensions - SMD-1



NOTES:

1. DIMENSIONING & TOLERANCING PER ASME Y14.5M–1994.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
4. DIMENSION INCLUDES METALLIZATION FLASH.
5. DIMENSION DOES NOT INCLUDE METALLIZATION FLASH.

PAD ASSIGNMENTS

MOSFET	SCHOTTKY SINGLE DIE	SCHOTTKY DUAL DIE
1 = DRAIN	1 = CATHODE	1 = CATHODE
2 = GATE	2 = COMMON ANODE	2 = ANODE 1
3 = SOURCE	3 = COMMON ANODE	3 = ANODE 2

IMPORTANT NOTICE

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